

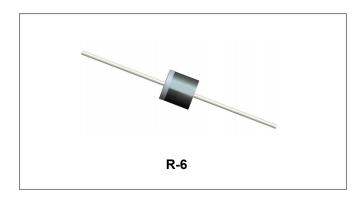




6A05 THRU 6A10

GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 6.0 Amperes



Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed: 250 ℃ /10 seconds,0.375"(9.5mm) lead length, 5 lbs. (2.3kg) tension
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: R-6 molded plastic
- Terminals: Plated axial leads, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 2.1 grams

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Type Number	Symbol	6A05	6A1	6A2	6A4	6A6	6A8	6A10	Units
Maximum repetitive peak reverse voltage Maximum DC blocking voltage	$V_{RRM} \ V_{DC}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at @T _A = 60°C	I _(AV)	6.0			А				
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	400			А				
Maximum instantaneous forward voltage at 6.0A	VF				0.95				V
Maximum DC reverse current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _R	10.0 400			μA				
Typical Junction Capacitance (Note 1)	CJ	150				pF			
Typical Thermal Resistance (Note 2)	R _{θJA}				10.0				°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +175				°C			

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

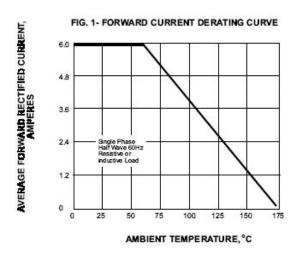
- 2. Thermal resistance from junction to ambient at 0.375"(9.5mm)lead length, P.C.B. mounted
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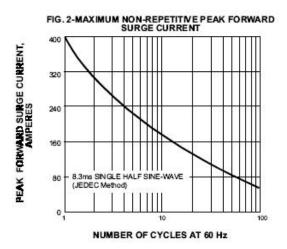


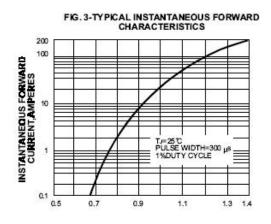


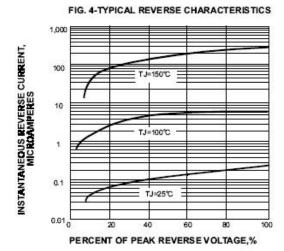


Ratings and Characteristics Curves

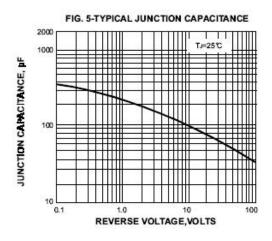


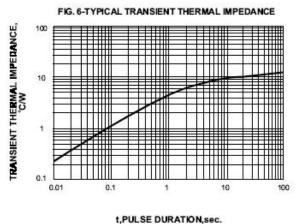












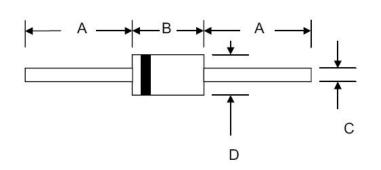
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Mechanical Dimensions R-6



OVMPOL	Millim	neters	Inches			
SYMBOL	Min.	Max.	Min.	Max.		
Α	24.0	-	0.940	-		
В	8.60	9.10	0.340	0.360		
С	1.2	1.3	0.048	0.052		
D	8.60	9.10	0.340	0.360		

Ordering Information

Device	Package	Shipping
6A05-6A10	R-6 (Pb-Free)	500pcs / Tape

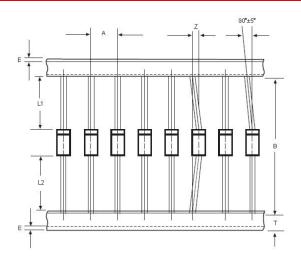
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



6A05 = Type Number

Carrier Tape Specification R-6



SYMBOL	Millimeters			
	Min.	Max.		
А	9.50	10.50		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
E	-	0.80		
IL1-L2I	-	1.0		

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